UNISONIC TECHNOLOGIES CO., LTD
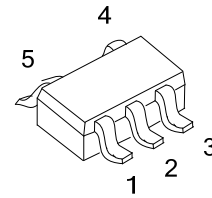
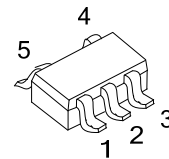## U74LVC1G34

CMOS IC

SINGLE BUFFER GATE

■ **DESCRIPTION**

The **U74LVC1G34** is a single buffer, it provides the function Y = A. This device has power-down protective circuit, preventing device destruction when it is powered down.

■ **FEATURES**

* Operate From 1.65V to 5.5V
* Inputs Accept Voltages to 5.5V
* I_{OFF} Supports Partial-Power-Down Mode
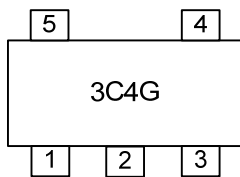* Low Power Dissipation
* Max t_{PD} of 3.5 ns at 3.3V

SOT-25

SOT-353

■ **ORDERING INFORMATION**

Ordering Number	Package	Packing
U74LVC1G34G-AF5-R	SOT-25	Tape Reel
U74LVC1G34G-AL5-R	SOT-353	Tape Reel

U74LVC1G34G-AF5-R

(1)Packing Type
(2)Package Type
(3)Green Package

(1) R: Tape Reel

(2) AF5: SOT-25, AL5: SOT-353

(3) G: Halogen Free and Lead Free

■ **MARKING**

3C4G

■ **PIN CONFIGURATION**

```
Vcc              Y
┌─5─┐         ┌─4─┐
│   ┌─────────┐   │
│   │         │   │
│   │         │   │
    └─1─┘ └─2─┘ └─3─┘
     NC    A    GND
```
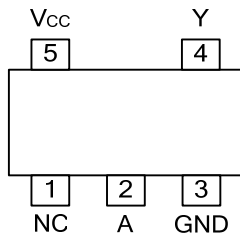
■ **FUNCTION TABLE**

INPUT(A)	OUTPUT(Y)
H	H
L	L

Note: H: HIGH voltage level; L: LOW voltage level.

■ **LOGIC DIAGRAM** (Positive Logic)
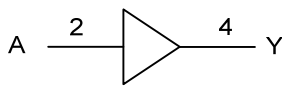
```
A ──2──▷──4── Y          A ──2──┌───┐──4── Y
                                │ 1 │
                                └───┘
   Logic Symbol              IEC Logic Symbol
```

U74LVC1G34
CMOS IC
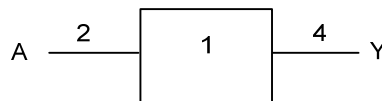
■ **ABSOLUTE MAXIMUM RATING** (T_A =25°C , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Supply Voltage		V_{CC}	-0.5 ~ +6.5	V
Input Voltage		V_{IN}	-0.5 ~ +6.5	V
Output Voltage	Output in the high or low state	V_{OUT}	-0.5 ~ V_{CC}+0.5	V
	Output in the high-impedance or power-off state		-0.5 ~ +6.5	V
V_{CC} or GND Current		I_{CC}	±100	mA
Continuous Output Current (V_{OUT}=0 to V_{CC})		I_{OUT}	±50	mA
Input Clamp Current (V_{IN}<0)		I_{IK}	-50	mA
Output Clamp Current (V_{OUT}<0)		I_{OK}	-50	mA
Operating Temperature		T_{OPR}	-40 ~ +85	°C
Storage Temperature Range		T_{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junctions to Ambient	SOT-25	θ_{JA}	230	°C/W
	SOT-353		350	

■ **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Supply Voltage	V_{CC}	Operating	1.65		5.5	V
		Data retention only	1.5			V
Input Voltage	V_{IN}		0		5.5	V
Output Voltage	V_{OUT}	High or low state	0		V_{CC}	V
High-Level Output Current	I_{OH}	V_{CC}=1.65V			-4	mA
		V_{CC}=2.3V			-8	mA
		V_{CC}=3V			-16	mA
		V_{CC}=3V			-24	mA
		V_{CC}=4.5V			-32	mA
Low-Level Output Current	I_{OL}	V_{CC}=1.65V			4	mA
		V_{CC}=2.3V			8	mA
		V_{CC}=3V			16	mA
		V_{CC}=3V			24	mA
		V_{CC}=4.5V			32	mA
Input Transition Rise or Fall Rate	t_R / t_F	V_{CC}=1.8V±0.15V, 2.5V±0.2V			20	ns/V
		V_{CC}=3.3V±0.3V			10	ns/V
		V_{CC}=5V±0.5V			10	ns/V

U74LVC1G34

■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
High-Level Input Voltage	V_{IH}	V_{CC}=1.65V ~ 1.95V		0.65*V_{CC}			V
		V_{CC}=2.3V ~ 2.7V		1.7			V
		V_{CC}=3V ~ 3.6V		2			V
		V_{CC}=4.5V ~ 5.5V		0.7*V_{CC}			V
Low-Level Input Voltage	V_{IL}	V_{CC}=1.65V ~ 1.95V				0.35*V_{CC}	V
		V_{CC}=2.3V ~ 2.7V				0.7	V
		V_{CC}=3V ~ 3.6V				0.8	V
		V_{CC}=4.5V ~ 5.5V				0.3*V_{CC}	V
High-Level Output Voltage	V_{OH}	I_{OH}=-100µA	V_{CC}=1.65 ~ 5.5V	V_{CC}-0.1			V
		I_{OH}=-4mA	V_{CC}=1.65V	1.2			V
		I_{OH}=-8mA	V_{CC}=2.3V	1.9			V
		I_{OH}=-16mA	V_{CC}=3.0V	2.4			V
		I_{OH}=-24mA	V_{CC}=3.0V	2.3			V
		I_{OH}=-32mA	V_{CC}=4.5V	3.8			V
Low-Level Output Voltage	V_{OL}	I_{OL}=100µA	V_{CC}=1.65 ~ 5.5V			0.1	V
		I_{OL}=4mA	V_{CC}=1.65V			0.45	V
		I_{OL}=8mA	V_{CC}=2.3V			0.3	V
		I_{OL}=16mA	V_{CC}=3.0V			0.4	V
		I_{OL}=24mA	V_{CC}=3.0V			0.55	V
		I_{OL}=32mA	V_{CC}=4.5V			0.55	V
Input Leakage Current	$I_{I(LEAK)}$	V_{IN}=5.5V or GND, V_{CC}=0 ~ 5.5V				±1	µA
Power OFF Leakage Current	I_{OFF}	V_{IN} or V_{OUT}=5.5V, V_{CC}=0V				±10	µA
Quiescent Supply Current	I_Q	V_{IN}=5.5V or GND, I_{OUT}=0 V_{CC}=1.65 ~ 5.5V				10	µA
Additional Quiescent Supply Current Per Input Pin	ΔI_Q	V_{CC}=3 ~ 5.5V, One input at V_{CC}-0.6V, Other inputs at V_{CC} or GND				500	µA
Input Capacitance	C_{IN}	V_{CC}=3.3V, V_{IN}=V_{CC} or GND			3.5		pF

■ **SWITCHING CHARACTERISTICS** (T_A=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Propagation delay from input (A) to output(Y)	t_{PLH} / t_{PHL}	V_{CC}=1.8±0.15V	C_L=15pF, R_L=1MΩ	2		9.9	ns
		V_{CC}=2.5±0.2V		1.5		6	ns
		V_{CC}=3.3±0.3V		1		3.5	ns
		V_{CC}=5±0.5V		1		2.9	ns
Propagation delay from input (A) to output(Y)	t_{PLH} / t_{PHL}	V_{CC}=1.8±0.15V, R_L=1KΩ	C_L=30pF	3.2		8.6	ns
		V_{CC}=2.5±0.2V, R_L=500Ω		1.5		4.4	ns
		V_{CC}=3.3±0.3V	C_L=50pF, R_L=500Ω	1.5		4.1	ns
		V_{CC}=5±0.5V		1		3.2	ns

■ **OPERATING CHARACTERISTICS** (T_A=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Power Dissipation Capacitance	C_{PD}	V_{CC}=1.8V	f=10MHz		16		pF
		V_{CC}=2.5V			16		pF
		V_{CC}=3.3V			16		pF
		V_{CC}=5V			18		pF

■ **TEST CIRCUIT AND WAVEFORMS**

From Output
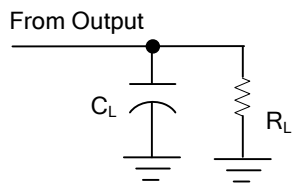
C_L R_L

TEST CIRCUIT

V_{CC}	INPUTS		V_M	C_L	R_L
	V_{IN}	t_R, t_F			
1.8V±0.15V	V_{CC}	≤2ns	$V_{CC}/2$	15pF	1MΩ
2.5V±0.2V	V_{CC}	≤2ns	$V_{CC}/2$	15pF	1MΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1MΩ
5V±0.5V	V_{CC}	≤2.5ns	$V_{CC}/2$	15pF	1MΩ
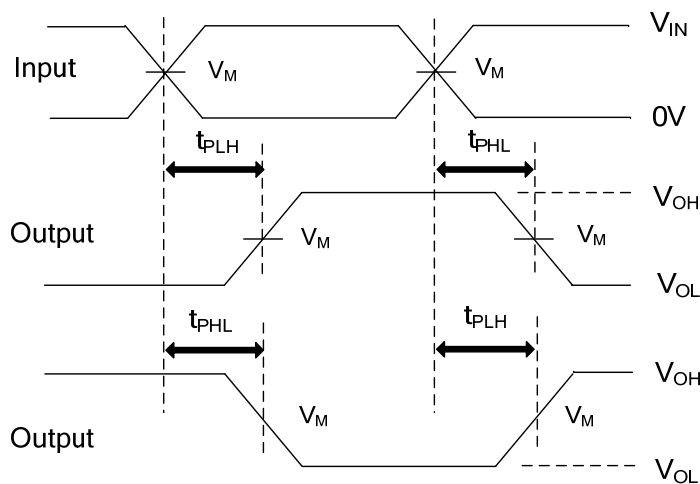
Input V_M V_M V_{IN} 0V

t_{PLH} t_{PHL}

Output V_M V_M V_{OH} V_{OL}

t_{PHL} t_{PLH}

Output V_M V_M V_{OH} V_{OL}

PROPAGATION DELAY TIMES
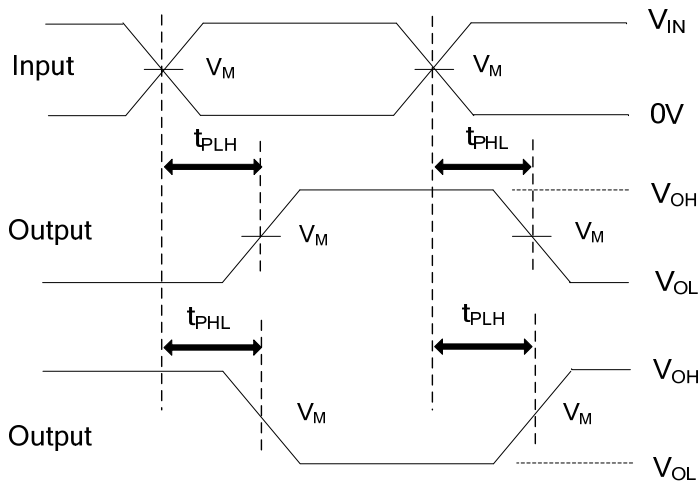
Note: C_L includes probe and jig capacitance.
All input pulses are supplied by generators having the following characteristics: P_{RR} ≤10MHz, Z_O = 50Ω.

■ **TEST CIRCUIT AND WAVEFORMS(Cont.)**

From Output
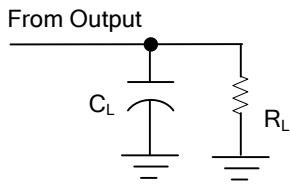
C_L R_L

TEST CIRCUIT

V_{CC}	INPUTS		V_M	C_L	R_L
	V_{IN}	t_R, t_F			
1.8V±0.15V	V_{CC}	≤2ns	$V_{CC}/2$	30pF	1KΩ
2.5V±0.2V	V_{CC}	≤2ns	$V_{CC}/2$	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V_{CC}	≤2.5ns	$V_{CC}/2$	50pF	500Ω

Input V_M V_M V_{IN} 0V

t_{PLH} t_{PHL}

Output V_M V_M V_{OH} V_{OL}

t_{PHL} t_{PLH}

Output V_M V_M V_{OH} V_{OL}

PROPAGATION DELAY TIMES

Note: C_L includes probe and jig capacitance.
All input pulses are supplied by generators having the following characteristics: P_{RR} ≤10MHz, Z_O = 50Ω.